

TPSI2240-Q1 1200V, 50mA, Automotive Reinforced Solid-State Relay With Avalanche Protection

1 Features

- Qualified for automotive applications
 - AEC-Q100 grade 1: –40 to 125°C T_A
- Low EMI:
 - Meets CISPR25 class 5 performance with no additional components
- Integrated avalanche rated MOSFETs
 - Designed and qualified for reliability for dielectric withstand testing (Hi-Pot)
 - TPSI2240-Q1 I_{AVA} = 1mA for 60s pulses
 - TPSI2240T-Q1 I_{AVA} = 3mA for 60s pulses
 - 1200V standoff voltage
 - R_{ON} = 130Ω (T_J = 25°C)
 - T_{ON}, T_{OFF} < 700μs
 - I_{OFF} = 1.22μA at 1000V (T_J = 105°C)
- Low primary side supply current
 - 5mA ON state current
 - 3.5μA OFF state current (T_J = 25°C)
- [Functional Safety Capable](#)
 - [Documentation available](#) to aid in ISO 26262 and IEC 61508 system design
- Robust isolation barrier:
 - > 30 year projected lifetime at 1000V_{RMS} / 1500V_{DC} working voltage
 - Reinforced Isolation rating, V_{ISO}, up to 3750V_{RMS}
- SOIC 11-pin (DWQ) package with wide pins for improved thermal performance
 - Creepage and clearance ≥ 8mm (primary-secondary)
 - Creepage and clearance ≥ 6mm (across switch terminals)
- [Safety-related certifications](#)
 - (Planned) DIN EN IEC 60747-17 (VDE 0884-17)
 - (Planned) UL 1577 component recognition program

2 Applications

- [Solid state relay](#)
- [Hybrid, electric, and power train systems](#)
- [Battery Management Systems \(BMS\)](#)

- [Energy Storage Systems \(ESS\)](#)
- [Solar energy](#)
- [Onboard charger](#)
- [EV charging infrastructure](#)
- See also the [TI Reference Designs](#) related to these applications.

3 Description

The TPSI2240-Q1 is an isolated solid state relay designed for high voltage automotive and industrial applications. The TPSI2240-Q1 uses TI's high reliability capacitive reinforced isolation technology in combination with internal back-to-back MOSFETs to form an integrated solution requiring no secondary side power supply.

The primary side of the device is powered by only 5mA of input current and incorporates a fail-safe EN pin preventing any possibility of back powering the VDD supply. In most applications, the VDD pin of the device should be connected to a system supply between 5V – 20V and the EN pin of the device should be driven by a GPIO output with logic HI between 2.1V – 20V. In other applications, The VDD and EN pins could be driven together directly from the system supply or from a GPIO output. All control configurations of the TPSI2240-Q1 do not require additional external components such as a resistor and/or low side switch that are typically required in photo relay solutions.

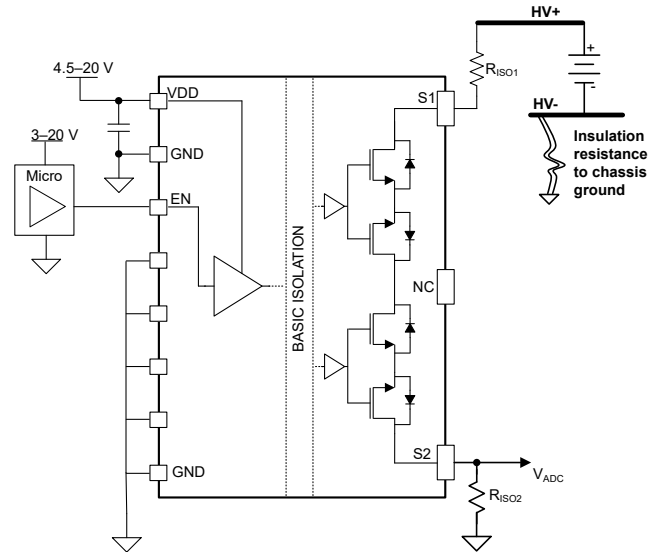
The secondary side consists of back-to-back MOSFETs with a standoff voltage of ±1.2kV from S1 to S2. The TPSI2240-Q1 MOSFET's avalanche robustness and thermally conscious package design, allow it to robustly support system level dielectric withstand testing (HiPot) and DC fast charger surge currents of up to 1mA without requiring any external components.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
TPSI2240x-Q1	DWQ (SOIC 11 pin)	10.3mm × 7.5mm

- (1) For all available packages, see the orderable addendum at the end of the data sheet.





TPSI2240-Q1 Simplified Application Schematic

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4 Device Comparison

Table 4-1. Device Comparison

DEVICE NAME	AVALANCHE PROTECTION MODE	MAXIMUM AVALANCHE CURRENT (60s)
TPSI2240-Q1	Standard Avalanche Protection	1.0mA
TPSI2240T-Q1	Thermal Avalanche Protection	3.0mA

5 Pin Configuration and Functions

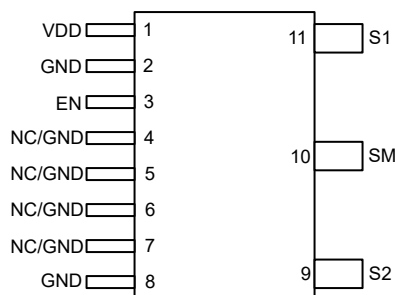


Figure 5-1. TPSI2240-Q1 DWQ Package, 11-Pin SOIC (Top View)

Table 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NO.	NAME		
1	VDD	P	Power supply for primary side
2	GND	GND	Ground supply for primary side
3	EN	I	Active high switch enable signal
4	NC/GND	NC/GND	Internally connected, connect externally to ground or leave floating
5	NC/GND	NC/GND	Internally connected, connect externally to ground or leave floating
6	NC/GND	NC/GND	Internally connected, connect externally to ground or leave floating
7	NC/GND	NC/GND	Internally connected, connect externally to ground or leave floating
8	GND	GND	Internally connected to GND, connect externally to ground or leave floating
9	S2	I/O	Switch input
10	NC	NC	No connect
11	S1	I/O	Switch input

(1) P = power, I = input, O = output, GND = ground, NC = no connect

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

PARAMETER		MIN	MAX	UNIT
V _{VDD}	Primary side supply voltage ⁽²⁾	−0.3	20.7	V
V _{EN}	Enable voltage ⁽²⁾	−0.3	20.7	V
I _{S1,S2}	Switch current, S1/S2	−55	55	mA
I _{AVA,S1,S2}	Repetitive avalanche rating, 60s pulse, TPSI2240, S1/S2 ⁽³⁾	−1	1	mA
I _{AVA,S1,S2}	Repetitive avalanche rating, 60s pulse, TPSI2240T, TAP, S1/S2 ⁽³⁾	−3	3	mA
T _J	Junction temperature	−40	150	°C
T _{stg}	Storage temperature	−65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) Voltage values are with respect to GND.
- (3) 5 minutes accumulated over lifetime in increments of no longer than 60 second periods, duty cycle < 10%, TAP Mode

6.2 ESD Ratings

				VALUE	UNIT
HBM _{Prim}	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 2	Primary Side Pins No. 1-8	±2000	V
HBM _{Sec}		Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 1C	Secondary Side Pins No. 9-11	±1500	V
V _{ESD}	Electrostatic discharge	Contact discharge, per IEC 61000-4-2	Secondary Side Pins No. 9-11	±8000	V

- (1) AEC Q100-002 indicates that HBM stressing must be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	NOM	MAX	UNIT
V _{VDD}	Primary side supply voltage ⁽¹⁾	4.5		20	V
V _{EN}	Enable voltage ⁽¹⁾	0		20	V
V _{S2-S1}	Switch input voltage	–1200		1200	V
I _{S1,S2}	Switch current	–50		50	mA
T _A	Ambient operating temperature	–40		125	°C
T _J	Junction operating temperature	–40		150	°C

(1) Voltage values are with respect to GND.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		DEVICE	UNIT
		DWQ (SOIC)	
		11 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	TBD	°C/W
R _{θJB}	Junction-to-board thermal resistance	TBD	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	TBD	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	TBD	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	TBD	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Power Ratings

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P _D	Maximum power dissipation, total	V _{VDD} = 5 V, V _{EN} = 5 V peak to peak, V _{S1-S2} = 1200V, R _{S1} = 500kΩ f _{EN} = 1Hz square wave			TBD	mW
P _{D_P}	Maximum power dissipation (primary)				TBD	mW
P _{D_S}	Maximum power dissipation (secondary)				TBD	mW

6.6 Insulation Specifications

PARAMETER		TEST CONDITIONS	VALUE	UNIT
IEC 60664-1				
CLR	External clearance ⁽¹⁾	Shortest terminal-to-terminal distance through air	>8	mm
CPG	External Creepage ⁽¹⁾	Shortest terminal-to-terminal distance across the package surface	>8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	>15.4	μm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	>600	V
	Material Group	According to IEC 60664-1	I	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 300 V _{RMS}	I-IV	
		Rated mains voltage ≤ 600 V _{RMS}	I-III	
		Rated mains voltage ≤ 1000 V _{RMS}	I-II	
DIN V VDE 0884-11:2017-01 ⁽²⁾ , IEC 60747-17:2020				
V _{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	1414	V _{PK}
V _{IOWM}	Maximum isolation working voltage	AC voltage (sine wave)	1000	V _{RMS}
		DC voltage	1500	V _{DC}
V _{IOTM}	Maximum transient isolation voltage	V _{TEST} = V _{IOTM} , t = 60 s (qualification)	6700	V _{PK}
		V _{TEST} = 1.2 × V _{IOTM} , t = 1 s (100% production)	8059	V _{PK}
V _{IMP}	Maximum Impulse voltage ⁽⁶⁾	Tested in air per IEC 62638-1, 1.2/50 μs waveform,	7690	V _{PK}
V _{IOSM}	Maximum surge isolation voltage ⁽³⁾	Tested in oil per IEC 62638-1, 1.2/50 μs waveform, V _{TEST} = 1.3 × V _{IOSM} (qualification)	10000	V _{PK}
q _{pd}	Apparent charge ⁽⁴⁾	Method a: After I/O safety test subgroup 2/3,V _{ini} = V _{IOTM} , t _{ini} = 60 s; V _{pd(m)} = 1.2 × V _{IORM} , t _m = 10 s	≤5	pC
		Method a: After environmental tests subgroup 1, V _{ini} = V _{IOTM} , t _{ini} = 60 s; V _{pd(m)} = 1.6 × V _{IORM} , t _m = 10 s	≤5	
		Method b1: At routine test (100% production) and preconditioning (type test), V _{ini} = V _{IOTM} , t _{ini} = 1 s; V _{pd(m)} = 1.875 × V _{IORM} , t _m = 1 s	≤5	
C _{IO}	Barrier capacitance, input to output ⁽⁵⁾	V _{IO} = 0.4 × sin (2πft), f = 1 MHz	4	pF
R _{IO}	Insulation resistance, input to output ⁽⁵⁾	V _{IO} = 500 V, T _A = 25°C	>10 ¹²	Ω
		V _{IO} = 500 V, 100°C ≤ T _A ≤ 125°C	>10 ¹¹	
		V _{IO} = 500 V at T _S = 150°C	>10 ⁹	
	Pollution degree		2	
	Climatic category		40/150/21	
UL 1577				
V _{ISO}	Withstand isolation voltage	V _{TEST} = V _{ISO} , t = 60 s (qualification) V _{TEST} = 1.2 × V _{ISO} , t = 1 s (100% production)	4750	V _{RMS}
Misc.				
V _{ISO}	Withstand isolation voltage		6700	V _{DC}

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a printed-circuit board are used to help increase these specifications.
- (2) This coupler is suitable for *safe electrical insulation* only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
- (3) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- (4) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (5) All pins on each side of the barrier tied together creating a two-pin device.

- (6) Testing is carried out in air to determine the intrinsic surge immunity of the package.

6.7 Safety-Related Certifications

VDE	CSA	UL	CQC	TUV
Plan to certify according to DIN EN IEC 60747-17 (VDE 0884-17)	Not Planned, contact TI to request.	Plan to certify according to UL 1577 Component Recognition Program	Not Planned, contact TI to request.	Not Planned, contact TI to request.
Reinforced insulation; Maximum transient isolation voltage, 6700 V _{PK} ; Maximum repetitive peak isolation voltage, 1414 V _{PK} ; Maximum surge isolation voltage, 10000 V _{PK}		Single protection, 4750 V _{RMS}		
Certificate planned		Certificate planned		

6.8 Safety Limiting Values

PARAMETER ^{(1) (2)}		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _S	Safety VDD Current	R _{θJA} = 70°C/W, V _{VDD} = 20 V, T _J = 150°C, T _A = 25°C			TBD	mA
	Safety Switch Current (On State)	R _{θJA} = 70°C/W, V _{VDD} = 20 V, T _J = 150°C, T _A = 25°C			TBD	
	Safety Switch Current (Off State, 5 second)	R _{θJA, EVM, 5S} ⁽³⁾ = 30°C/W, V _{VDD} = 0 V, T _J = 150°C, T _A = 25°C			TBD	
	Safety Switch Current (Off State, 60 second)	R _{θJA, EVM, 60S} ⁽³⁾ = 52°C/W, V _{VDD} = 0 V, T _J = 150°C, T _A = 25°C			TBD	
P _S	Safety input, output, or total power	R _{θJA} = 70°C/W, T _J = 150°C, T _A = 25°C.			TBD	W
T _S	Maximum safety temperature				150	°C

- (1) Safety limiting intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.
- (2) The safety-limiting constraint is the maximum junction temperature specified in the data sheet. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the [Thermal Information](#) table is that of a device installed on a high-K test board for leaded surface-mount packages. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.
- (3) Assuming PCB layout similar to EVM in Layout Guideline section

6.9 Electrical Characteristics

Unless otherwise noted, all minimum/maximum specifications are over recommended operating conditions. All typical values are measured at $T_J = 25^\circ\text{C}$, $V_{DD} = 5\text{ V}$, $V_{EN} = 5\text{ V}$.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
PRIMARY SIDE SUPPLY (VDD)						
V _{UVLO_R}	VDD undervoltage threshold rising	VDD rising	4.1	4.3	4.5	V
V _{UVLO_F}	VDD undervoltage threshold falling	VDD falling	4.0	4.2	4.45	V
V _{UVLO_HYS}	VDD undervoltage threshold hysteresis		40	150		mV
I _{VDD_ON}	VDD current, device powered on	T _J = 25°C		5	11	mA
		−40°C ≤ T _J ≤ 150°C		5	12	mA
I _{VDD_OFF}	VDD current, 5 V, device powered off	V _{VDD} = 5 V, V _{EN} = 0 V, T _J = 25°C		3.5	8	μA
		V _{VDD} = 5 V, V _{EN} = 0 V, T _J = 105°C		6.3	11	μA
		V _{VDD} = 5 V, V _{EN} = 0 V, T _J = 125°C		7.6	16	μA
		V _{VDD} = 5 V, V _{EN} = 0 V, −40°C ≤ T _J ≤ 150°C			30	μA
	VDD current, 20 V, device powered off	V _{VDD} = 20 V, V _{EN} = 0 V T _J = 25°C		8	10.5	μA
		V _{VDD} = 20 V, V _{EN} = 0 V, T _J = 105°C		13	17	
		V _{VDD} = 20 V, V _{EN} = 0 V, T _J = 125°C		15	25	
		V _{VDD} = 20 V, V _{EN} = 0 V, −40°C ≤ T _J ≤ 150°C			40	
FET CHARACTERISTICS (S1, S2)						
R _{DS(on)}	On resistance	I _O = 2 mA, T _J = 25°C		130	175	Ω
		I _O = 2 mA, T _J = 85°C		176	235	
		I _O = 2 mA, T _J = 105°C		192	250	
		I _O = 2 mA, T _J = 125°C		210	275	
		I _O = 2 mA, −40°C ≤ T _J ≤ 150°C			300	
I _{OFF}	Off leakage, 1200 V	V = +/−1200 V, T _J = 25°C		0.058	0.25	μA
		V = +/−1200 V, T _J = 85°C			0.5	
		V = +/−1200 V, T _J = 105°C			1.5	
		V = +/−1200 V, T _J = 125°C			6	
		V = +/−1200 V, −40°C ≤ T _J ≤ 150°C			50	
	Off leakage, 1000 V	V = +/−1000 V, T _J = 25°C		0.055	0.25	μA
		V = +/−1000 V, T _J = 85°C			0.43	
		V = +/−1000 V, T _J = 105°C			1.22	
		V = +/−1000 V, T _J = 125°C			5.75	
		V = +/−1000 V, −40°C ≤ T _J ≤ 150°C			44	
V _{AVA}	Avalanche voltage	I _O = 10 μA, T _J = 25°C	1300	1550	V	
		I _O = 100 μA, T _J = 150°C	1300	1550		
C _{OSS}	S1, S2 capacitance	V _{S1,S2} = 0 V, SM float, F = 1 MHz		94		pF
T _{TAP1}	Thermal Avalanche Protection threshold (TPSI2240T-Q1 only)	Assertion	160			C
T _{TAP_END}	Thermal Avalanche Protection threshold (TPSI2240T-Q1 only)	De-assertion	85		125	C
LOGIC-LEVEL INPUT (EN)						
V _{IL}	Input logic low voltage		0.0		0.8	V
V _{IH}	Input logic high voltage		2.1		20.0	V

6.9 Electrical Characteristics (continued)

Unless otherwise noted, all minimum/maximum specifications are over recommended operating conditions. All typical values are measured at $T_J = 25^\circ\text{C}$, $V_{DD} = 5\text{ V}$, $V_{EN} = 5\text{ V}$.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{HYS}	Input logic hysteresis		100	250	300	mV
I_{IL}	Input logic low current	$V_{EN} = 0\text{ V}$	–0.1		0.1	μA
		$V_{EN} = 0.8\text{ V}$	0.1	0.68	6.5	μA
I_{IH}	Input logic high current	$V_{EN} = 5\text{ V}$	1.5	4.4	15	μA
		$V_{EN} = 10\text{ V}$	2	13	30	μA
		$V_{EN} = 20\text{ V}$	10	32	65	μA
I_{VDD_FS}	VDD fail-safe current	$V_{EN} = 20\text{ V}$, $V_{VDD} = 0\text{ V}$	–0.1	0	0.1	μA
R_{PD}	Pulldown resistance	Two point measurement, $V_{EN} = 0.5\text{ V}$ and $V_{EN} = 0.8\text{ V}$	589	1180	2050	k Ω
NOISE IMMUNITY						
CMTI	Common-mode transient immunity	$ V_{CM} = 1000\text{ V}$	100.0			V/ns

6.10 Switching Characteristics

Unless otherwise noted, all minimum/maximum specifications are over recommended operating conditions. All typical values are measured at $T_A = 25^\circ\text{C}$, $V_{DD} = 5\text{ V}$, $V_{EN} = 5\text{ V}$.

MODE	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Switching Characteristics							
EN switching	t _{PD_ON}	Input HI to Output voltage falling propagation delay	V _{IN} = 1000 V R _L = 1 MΩ		170	370	μs
	t _F	Output fall time			47	100	
	t _{ON}	Input HI to Output LO delay			220	440	
	t _{PD_OFF}	Input LO to Output voltage rising propagation delay			170	290	
	t _R	Output rise time			29	70	
	t _{OFF}	Input LO to Output HI delay			200	350	
EN and VDD switching	t _{PD_ON}	Input HI to Output voltage falling propagation delay	V _{IN} = 1000 V R _L = 1 MΩ		250	520	μs
	t _F	Output fall time			50	100	
	t _{ON}	Input HI to Output LO delay			310	590	
	t _{PD_OFF}	Input LO to Output voltage rising propagation delay			170	250	
	t _R	Output rise time			30	80	
	t _{OFF}	Input LO to Output HI delay			200	350	

7 Parameter Measurement Information

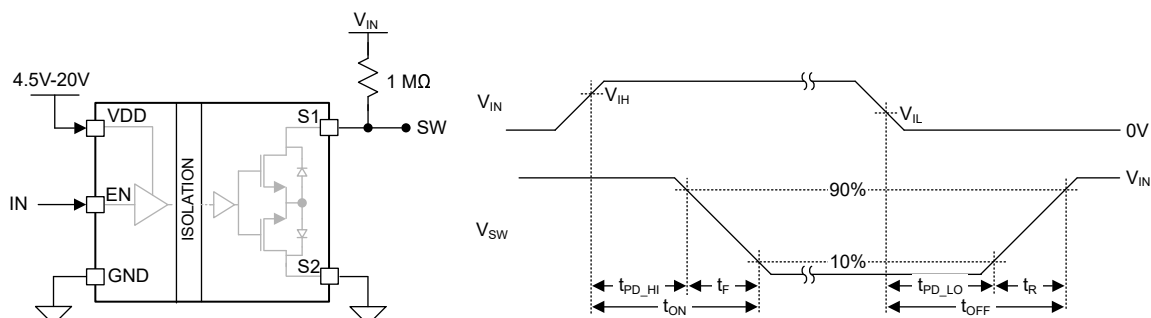


Figure 7-1. Timing Diagram, EN Switching

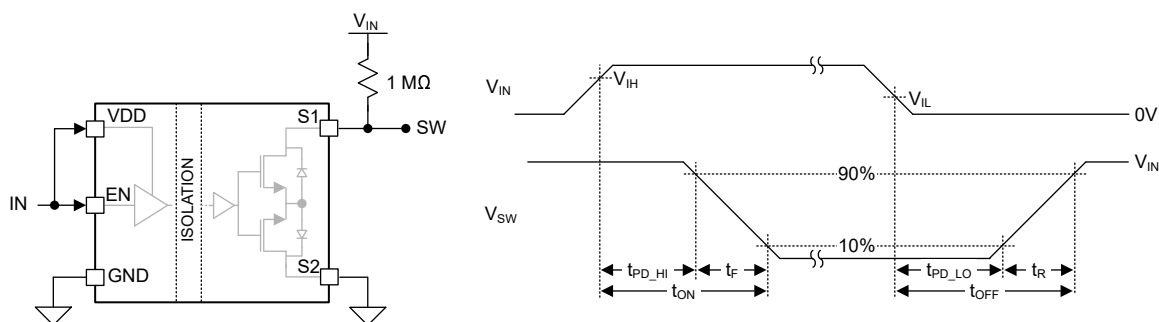


Figure 7-2. Timing Diagram, EN and VDD Switching

8 Detailed Description

8.1 Overview

The TPSI2240-Q1 is an isolated solid state relay designed for high voltage automotive and industrial applications. TI's high reliability capacitive isolation technology in combination with back-to-back MOSFETs form a completely integrated solution requiring no secondary side power supply.

As seen in the [Functional Block Diagram](#), the primary side consists of a driver which delivers power and enable logic information to each of the internal MOSFETs on the secondary side. The on-board oscillator controls the frequency of the driver's operation and the Spread Spectrum Modulation (SSM) controller varies the driver frequency to improve system EMI performance. When the enable pin is brought HI and the VDD voltage is above the UVLO threshold, the oscillator starts and the driver sends power and a logic HI across the barrier. When the enable pin is brought LO or the VDD voltage falls below the UVLO threshold, the driver is disabled. The lack of activity communicates a logic LO to the secondary side and the MOSFETs are disabled.

Each MOSFET on the secondary side has a dedicated full-bridge rectifier to form its local power supply and a receiver. The receiver determines the logic state delivered from the primary side through the capacitive isolation barrier and uses a slew rate controlled driver to drive the MOSFET's gate. Each receiver performs signal conditioning on the signals received across the barrier in order to filter common mode interference and ensure that the MOSFETs are controlled according to the logic sent by the primary side driver and the system.

The avalanche robust MOSFETs and the thermal benefits of the widened pins on the 11 DWQ package enable the TPSI2240-Q1 to support dielectric withstand testing (HiPot) and DC fast high charger surge currents without requiring any external protection components. The Thermal Avalanche Protection (TAP) feature included in the TPSI2240T-Q1 version of the device further improves the avalanche current capability by monitoring the junction temperature and enabling the MOSFETs to keep the temperature in a safe operating range allowing it to support a higher avalanche current.

8.2 Functional Block Diagram

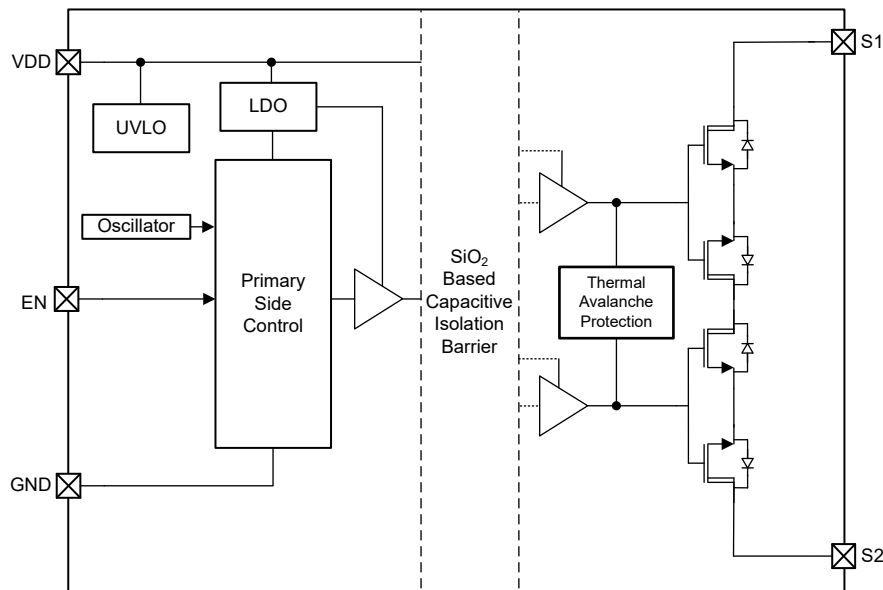


Figure 8-1. TPSI2240-Q1 Block Diagram

8.3 Feature Description

8.3.1 Avalanche Robustness

When the voltage between the S1 and S2 pins exceeds $\pm 1200\text{V}$ the secondary side MOSFETs could enter an avalanche mode of operation. The MOSFETs and the 11 DWQ package have been designed and qualified to be robust in this mode of operation to support Dielectric Withstand Testing (HiPot). To help ensure the thermal performance of the the system in this mode of operation, refer to the PCB Layout Guidelines.

8.4 Device Functional Modes

Table 8-1. Device Functional Modes

VDD	EN	S1-S2 State	COMMENTS
Powered Up ⁽¹⁾	L	OFF	VDD current is in OFF state range.
	H	ON	VDD current is in ON state range.
Powered Down ⁽²⁾	L	OFF	VDD current is in OFF state range.
	H	OFF	Primary side analog is powered on, VDD current is between OFF state and ON state ranges.

(1) VDD ≥ VDD undervoltage rising threshold.

(2) VDD ≤ VDD undervoltage falling threshold.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The TPSI2240-Q1 is a 1200V, 50mA automotive isolated switch optimized for high voltage switching in measurement applications, especially those that require switching across an isolation barrier or galvanically isolated domain. Common end equipments include energy storage systems (ESS), solar panel arrays, EV chargers, and EV battery management systems. The device enables the system designer to reduce cost and improve reliability by replacing mechanical relays and optically isolated devices.

The TPSI2240-Q1's enable input is fail safe and does not need to be driven from the same domain as the VDD pin supply.

The TPSI2240-Q1 supports an input voltage range of 4.5V to 20V on the VDD primary supply pin and a logic high of 2.1V to 20V on the enable pin. The secondary side supports high voltage switching from –1200V to 1200V.

TI Reference Designs

The TI reference designs linked below are a helpful introduction to high voltage applications using the TPSI2240-Q1. To maximize the thermal performance of the TPSI2240-Q1 for dielectric withstand testing (HiPot), please follow the [Layout Guidelines](#) contained within this datasheet.

- [TIDA-010232: High Voltage Insulation Monitoring](#)
- [TIDA-01513: Automotive High Voltage and Isolation Leakage Measurements](#)

9.2 Typical Application

Insulation Resistance Monitoring

In high voltage applications such as electric vehicle systems, the high voltage battery pack is intentionally isolated from the chassis domain of the car to protect the driver and prevent damage to electrical components. These systems actively monitor the integrity of this insulation to ensure the safety of the system throughout its lifetime. This active monitoring is referred to as insulation resistance monitoring (also known as isolation check, insulation check, isolation monitoring, insulation monitoring, and residual current monitoring (RCM)) and is performed by measuring the resistances from each of the battery terminals to the chassis ground, illustrated below as R_{ISOP} and R_{ISON} .

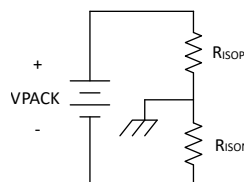


Figure 9-1. Insulation Resistance Model

There are multiple design architectures using the TPSI2240-Q1 to measure these insulation resistances, R_{ISOP} and R_{ISON} . Some architectures employ a microcontroller that performs measurements from the high voltage domain, which will be referred to in this document as the Battery V- Reference architecture. Others use a microcontroller in the low voltage domain, which will be referred to in this document as the Chassis Ground Reference architecture. The primary difference between the two architectures is the node that the MCU uses as its GND reference. An example of a Battery V- MCU is the [BQ79731-Q1 UIR sensor](#).

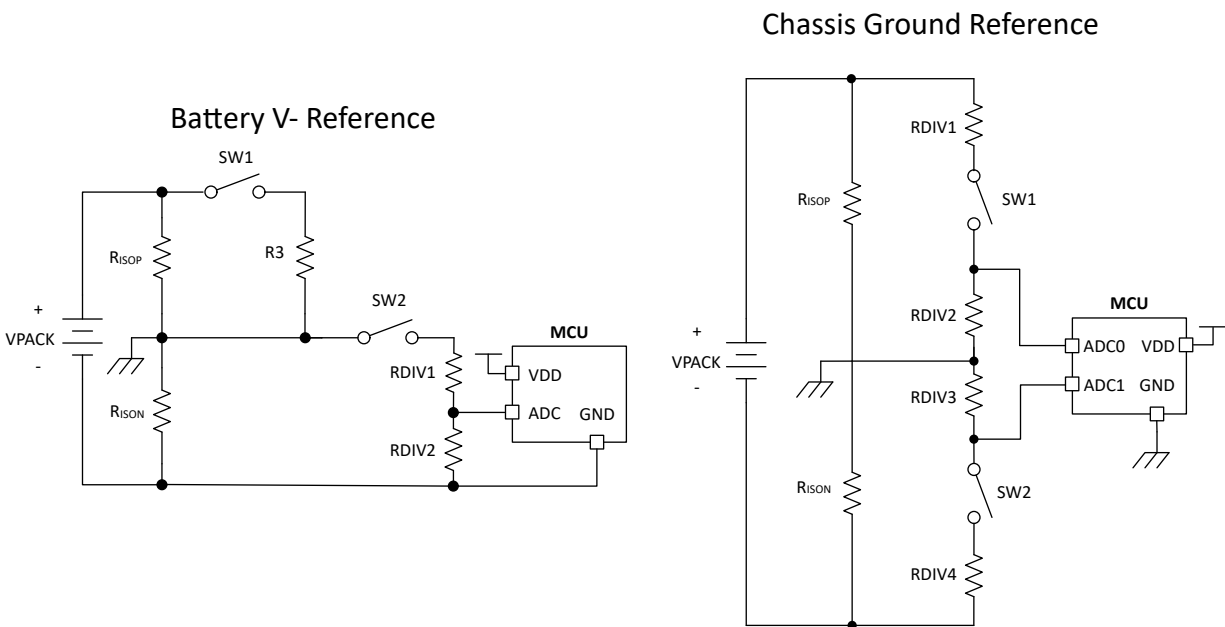


Figure 9-2. Different MCU ADC Reference Examples

The two following sections demonstrate the measurement algorithms and the systems of equations used to calculate the isolation resistances using each architecture.

Battery V- Reference Example

A Battery V- Reference architecture is shown below with the TPSI2240-Q1 illustrated as a switch (SW1 and SW2). SW2 initiates a connection between the chassis and PACK- and enables the measurement path to the ADC. SW1 initiates a connection between the chassis and the PACK+. RDIV1 and RDIV2 form a divider which scales the measured voltages down to the appropriate ADC range.

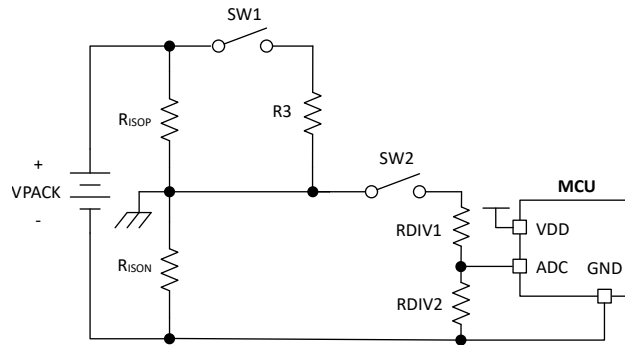


Figure 9-3. Battery V- Reference Architecture

Two ADC measurements must be taken in order to obtain enough information to calculate the two unknown isolation resistances. The first measurement is taken with SW1 open and SW2 closed. The second measurement is taken with SW1 closed and SW2 closed. With these two measurements it is possible to solve the system of equations and calculate R_{ISOP} and R_{ISON} .

In the following example the voltage on the chassis ground is arbitrarily referred to as V_{RISONx} .

For the first ADC measurement SW2 is closed as shown below and the following equations relate the ADC voltage to the other parameters in the system in this condition:

- V_{ADC1} measurement 1: SW1 open, SW2 closed

$$V_{RISON1} = V_{PACK} \times \frac{R_{ISON} \parallel (R_{DIV1} + R_{DIV2})}{R_{ISOP} + (R_{ISON} \parallel (R_{DIV1} + R_{DIV2}))} \quad (1)$$

$$V_{ADC1} = V_{RISON1} \times \frac{R_{DIV2}}{R_{DIV1} + R_{DIV2}} \quad (2)$$

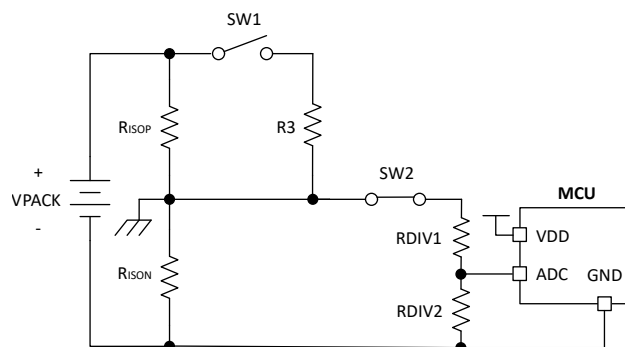


Figure 9-4. Battery V- Reference Switch Positions for ADC1 Measurement

For the second ADC measurement SW1 and SW2 are closed as shown below and the following equations relate the ADC voltage to the other parameters in the system in this condition:

- V_{ADC2} measurement 2: SW1 closed, SW2 closed

$$V_{RISON2} = V_{PACK} \times \frac{R_{ISON} || (R_{DIV1} + R_{DIV2})}{(R_{ISOP} || R_3) + (R_{ISON} || (R_{DIV1} + R_{DIV2}))} \quad (3)$$

$$V_{ADC2} = V_{RISON2} \times \frac{R_{DIV2}}{R_{DIV1} + R_{DIV2}} \quad (4)$$

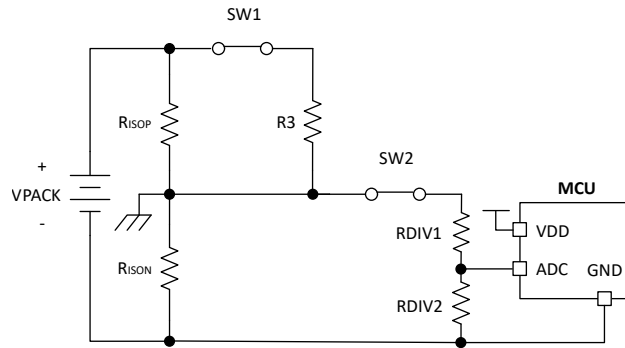


Figure 9-5. Battery V- Reference Switch Positions for ADC2 Measurement

Chassis Ground Reference Example

A Chassis Ground Reference architecture is shown below. SW1 and SW2 initiate connections to the PACK+ and PACK-, and enable their corresponding measurement paths to their ADCs through their corresponding resistor dividers. RDIV1, RDIV2, RDIV3, and RDIV4 scale the measured voltages down to the appropriate ADC ranges.

This first measurement is taken with SW1 closed and SW2 open and the second measurement is taken with SW1 open and SW2 closed.

- VADC1: SW1 closed, SW2 open

$$V_{ADC1} = V_{RDIV2} = V_{PACK} \frac{(R_{ISOP} || (R_{DIV1} + R_{DIV2}))}{(R_{ISOP} || (R_{DIV1} + R_{DIV2}) + R_{ISON})} \times \frac{R_{DIV2}}{R_{DIV1} + R_{DIV2}} \quad (5)$$

- VADC2: SW1 open, SW2 closed

$$V_{ADC2} = V_{RDIV3} = -V_{PACK} \frac{(R_{ISON} || (R_{DIV3} + R_{DIV4}))}{(R_{ISON} || (R_{DIV3} + R_{DIV4}) + R_{ISOP})} \times \frac{R_{DIV3}}{R_{DIV3} + R_{DIV4}} \quad (6)$$

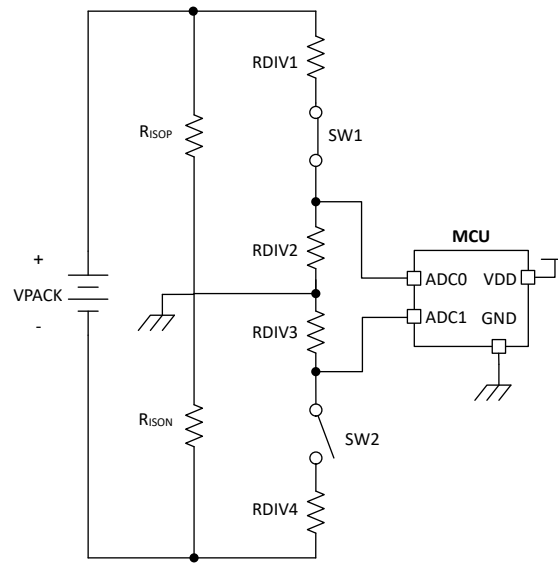


Figure 9-6. Chassis Ground Reference Switch Positions for ADC1 Measurement

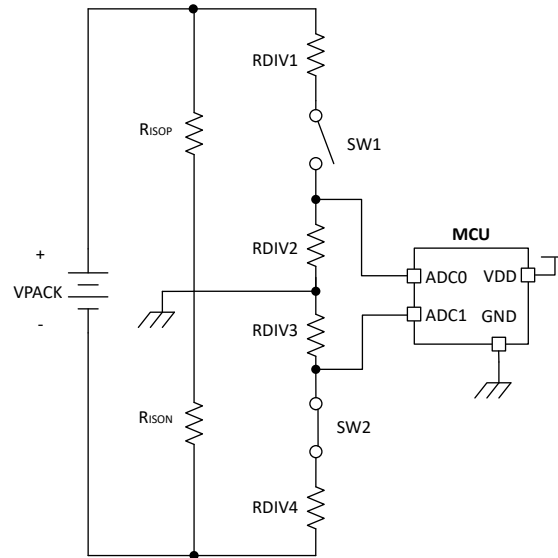


Figure 9-7. Chassis Ground Reference Switch Positions for ADC2 Measurement

Battery V- Reference and Chassis Ground Reference Architectures with the TPSI2240-Q1

The circuits in [Figure 9-8](#) and [Figure 9-9](#) demonstrate how to connect the TPSI2240-Q1 as a switch in each of the architectures above.

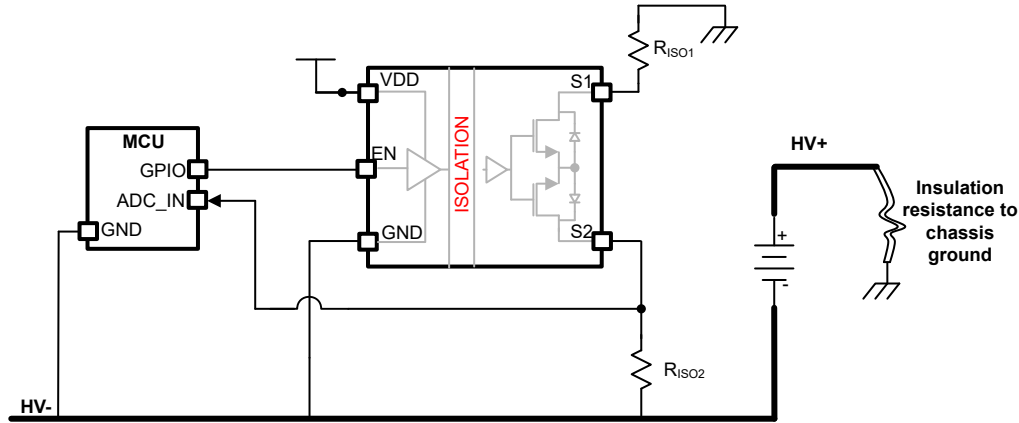


Figure 9-8. TPSI2240-Q1 Insulation Resistance Monitoring – Battery V- Reference

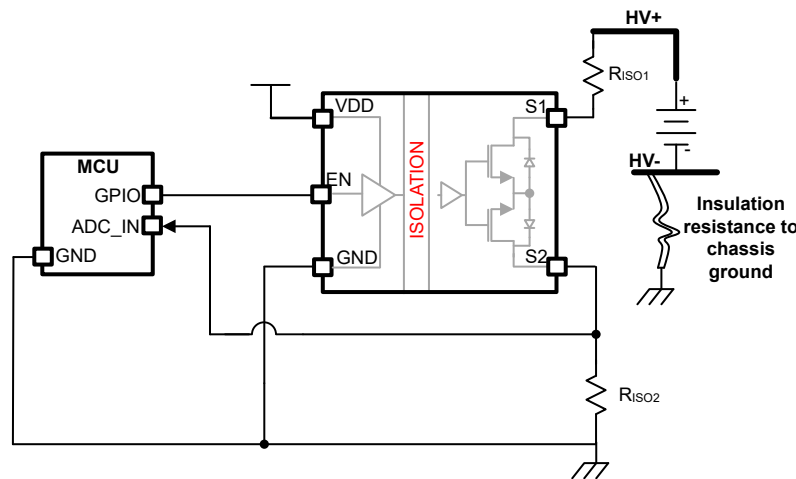


Figure 9-9. TPSI2240-Q1 Insulation Resistance Monitoring – Chassis Ground Reference

9.2.1 Dielectric Withstand Testing (HiPot)

The TPSI2240-Q1 is specifically designed to support dielectric withstand testing. In a high voltage system, a dielectric withstand test (HiPot) may be administered during the characterization, production or maintenance of the system to validate the reliability of the insulation barriers and galvanically isolated domains it contains. These withstand voltage tests intentionally stress the components spanning these domains and put them in an overvoltage condition. MOSFETs that are placed under these overvoltage conditions will enter avalanche mode and begin conducting current at a high voltage, dissipating high power and heating up. TPSI2240T-Q1 integrates Thermal Avalanche Protection (TAP). When the internal temperature of the IC increases beyond T_{TAP} this mode will enable. In this mode, the device will enable and disable the main power FET to regulate its internal temperature and be able to sustain higher avalanche currents. The design and qualification of the TPSI2240T-Q1 was completed with this state in mind and supports up to 3mA I_{AVA} for 60 second intervals, while the TPSI2240-Q1 supports up to 1mA I_{AVA} for 60 second intervals.

The dielectric withstand test voltage (V_{HiPot}), the TPSI2240-Q1's avalanche voltage (V_{AVA}), and the resistance (R) in series with the TPSI2240-Q1 should be chosen to limit the avalanche current (I_{AVA}) to the corresponding current limit depending on the test duration. In addition, the PCB design should follow the recommendations in the [Layout Guidelines](#) section to ensure adequate thermal performance to keep the junction temperature (T_J) below the absolute maximum rating of the TPSI2240-Q1.

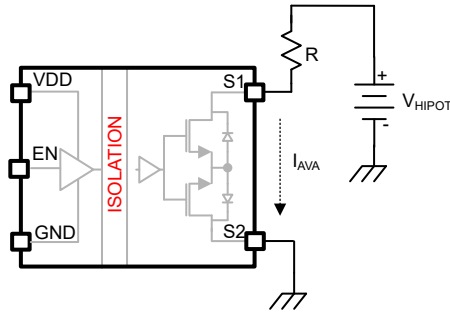


Figure 9-10. Dielectric Withstand Test (HiPot) - Simplified Schematic

9.2.2 Design Requirements

Table 9-1 lists the Design Requirements for a typical insulation resistance monitoring application using the Chassis Ground Reference architecture and the TPSI2240-Q1 for switching.

Table 9-1. Typical Design Parameters For Insulation Resistance Monitoring Using the TPSI2240-Q1 – Chassis Ground Reference Architecture

PARAMETER	VALUE
V _{PACK} Voltage (maximum)	1000V
Primary side supply (V _{VDD})	5V ±10 %
Dielectric withstand voltage test	3500V
	60s
Surge voltage (IEC61000-3-5)	2500V

9.2.3 Design Procedure - Chassis Ground Reference

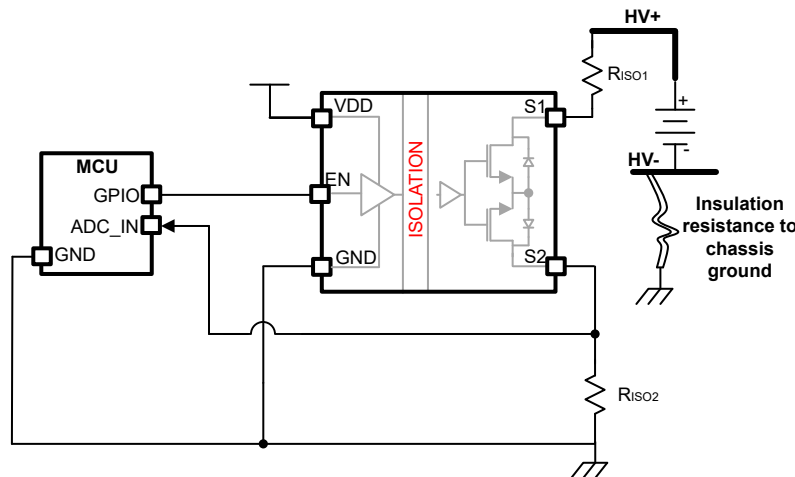


Figure 9-11. Chassis Ground Reference

R_{ISO1} Selection

In order to protect the TPSI2240-Q1, R_{ISO1} must be sized to limit the current in an overvoltage condition. The amount of resistance required to protect the TPSI2240-Q1 depends on the amount of overvoltage applied. For example, during a dielectric withstand voltage test (HiPot) of 3500V for 60 seconds, the S1 to S2 voltage will be clamped to 1300V (V_{AVA} minimum) by the TPSI2240-Q1 and the R_{ISO1} resistance required to keep the current under 1mA would be 2.2MΩ.

$$I_{AVA} = \frac{V_{HIPOT} - V_{AVA}}{R_{ISO1}} = \frac{3500V - 1300V}{2.2 \text{ M}\Omega} = 1.0mA \quad (7)$$

DC OVERVOLTAGE	R _{ISO1} MINIMUM (60 second intervals)
2000V	700kΩ
2500V	1200kΩ
3500V	2200kΩ
4300V	3000kΩ

9.3 Power Supply Recommendations

To ensure a reliable supply voltage, TI recommends that a 100nF ceramic capacitor be placed between the VDD pin and the GND pin of the TPSI2240-Q1. The capacitor should be placed as close to the device's VDD pin as possible < 10mm.

9.4 Layout

9.4.1 Layout Guidelines

Component placement:

Decoupling capacitors for the primary side VDD supply must be placed as close as possible to the device pins.

EMI considerations:

The TPSI2240-Q1 employs spread spectrum modulation (SSM), no additional system design considerations are required to meet the EMI performance needs.

High-voltage considerations:

The creepage from the primary side to the secondary side and the creepage from the S1 pin to S2 pin of the TPSI2240-Q1 should be maintained according to system requirements. It is most likely that the system designer will avoid any top layer PCB routing underneath the body of the package or between the S1, SM and S2 pins.

9.4.2 Layout Example

TPSI2240-Q1 EVM Circuit Layout

An example 2-layer circuit layout using the TPSI2240-Q1 is shown below.

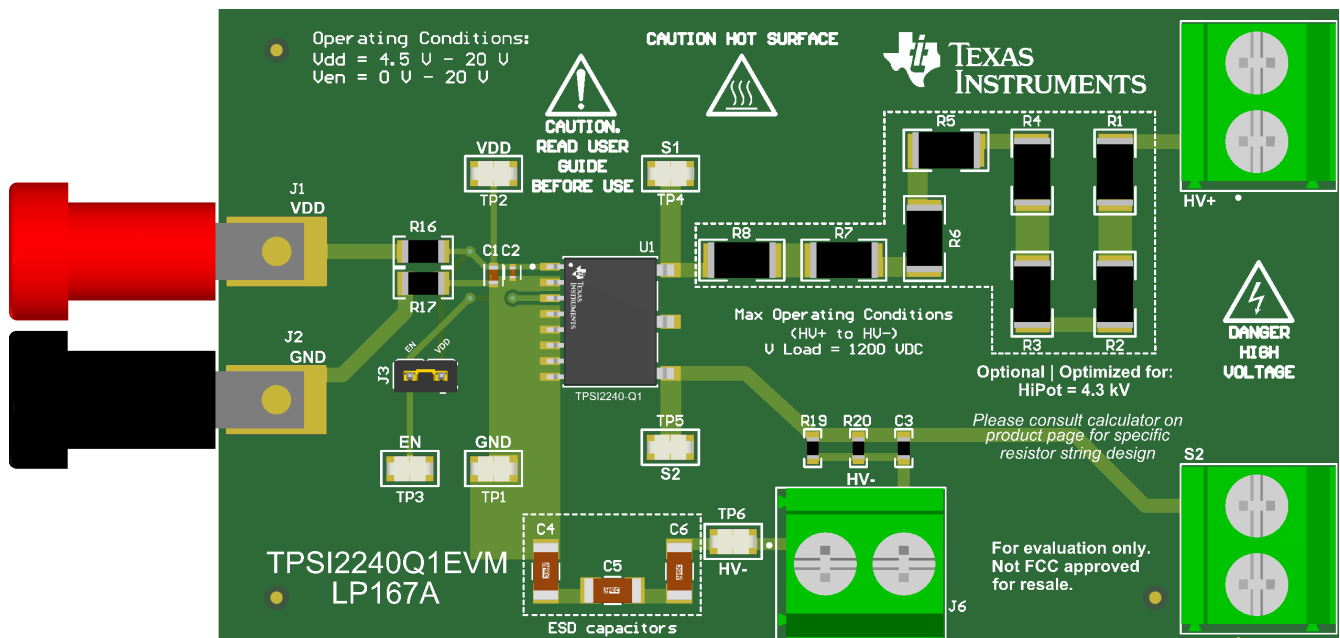


Figure 9-12. TPSI2240-Q1 EVM - Component View

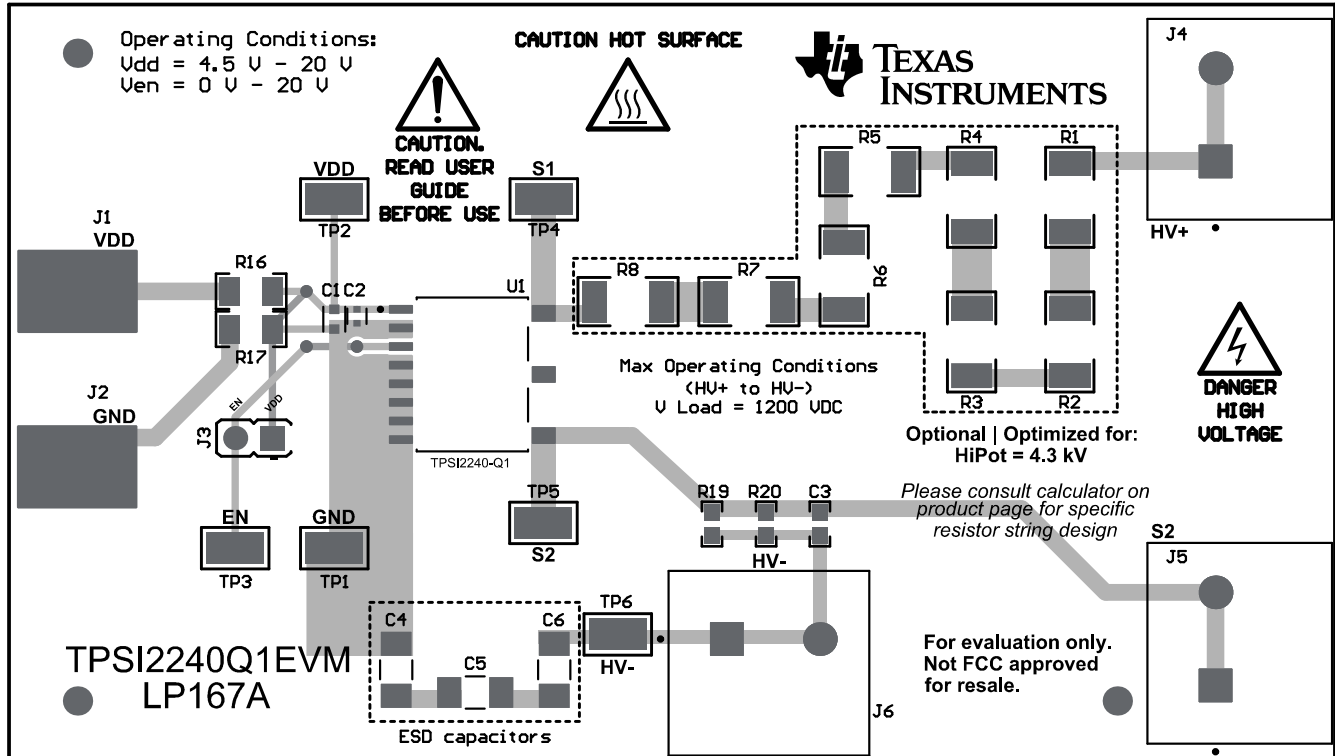


Figure 9-13. TPSI2240-Q1 EVM - Composite

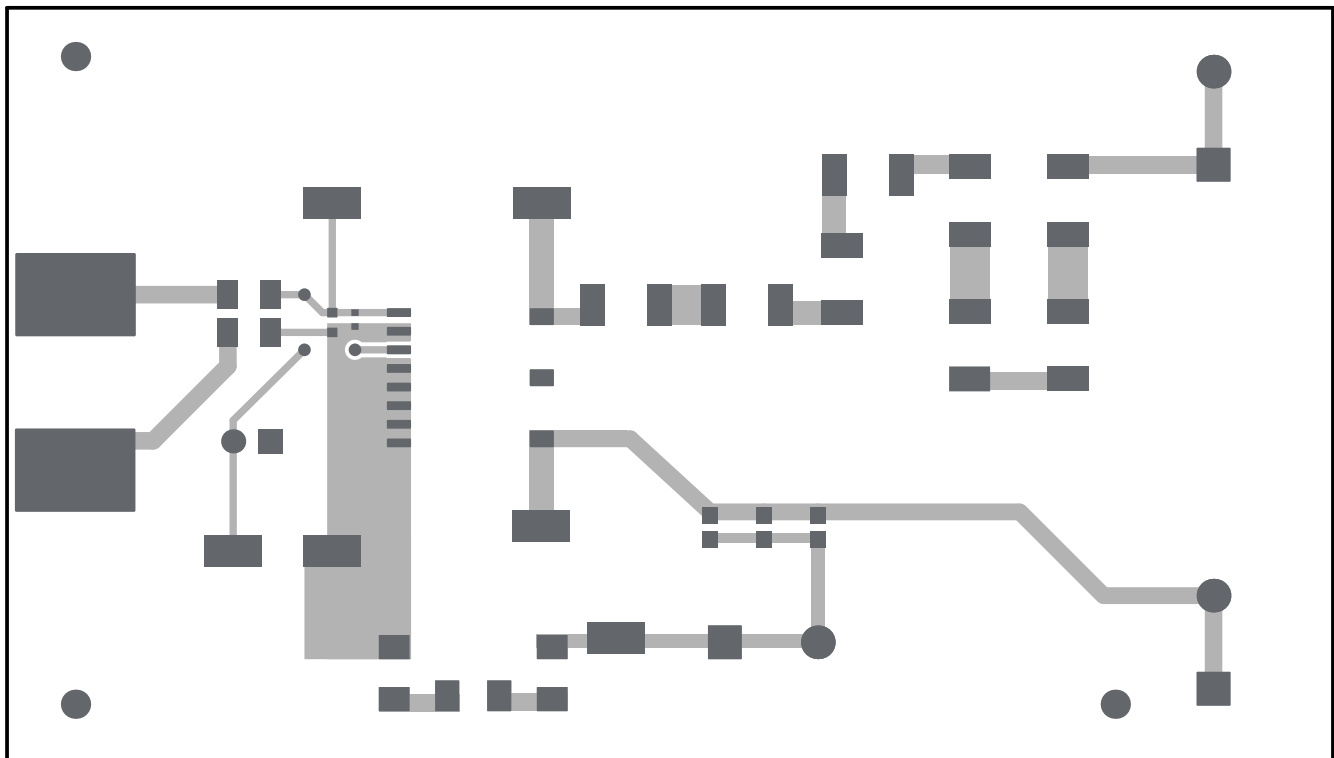


Figure 9-14. TPSI2240-Q1 EVM - Top Layer

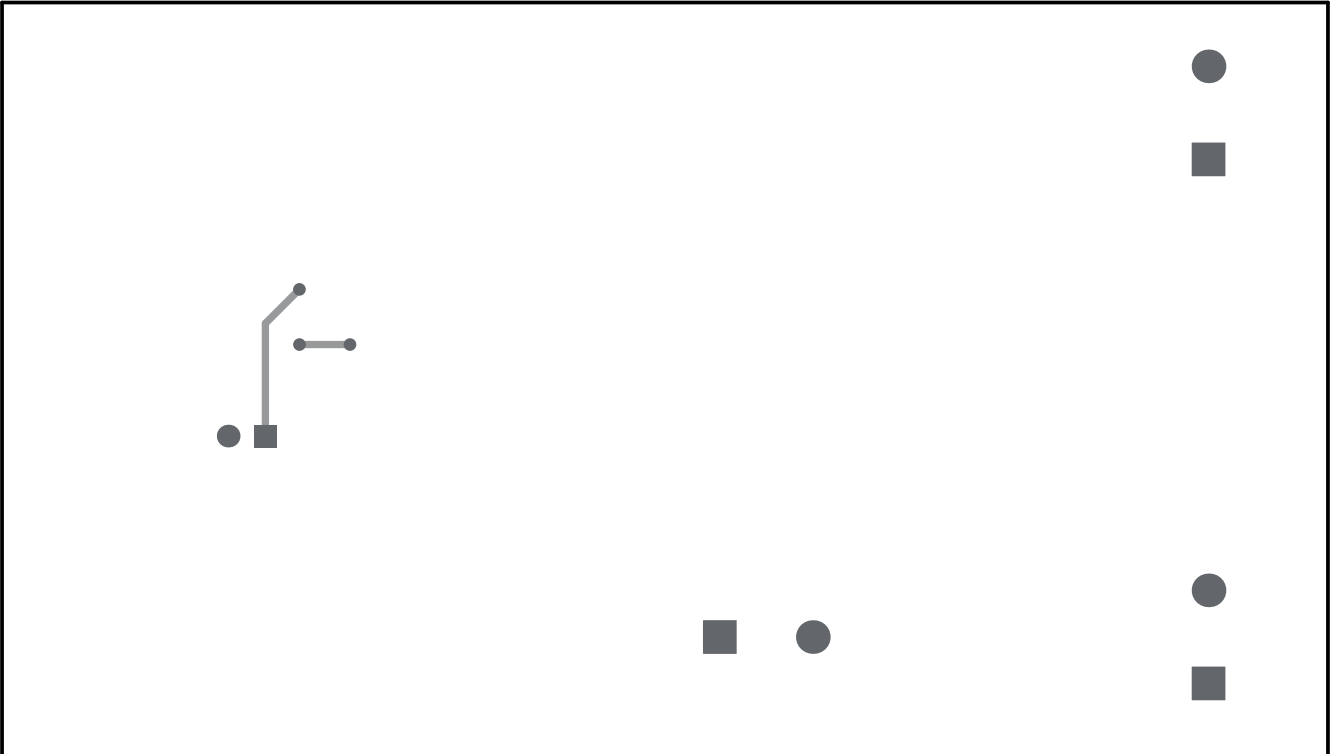


Figure 9-15. TPSI2240-Q1 EVM - Bottom Layer

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Third-Party Products Disclaimer

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10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

11 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
September 2025	*	Initial Release

12 Mechanical, Packaging, and Orderable Information

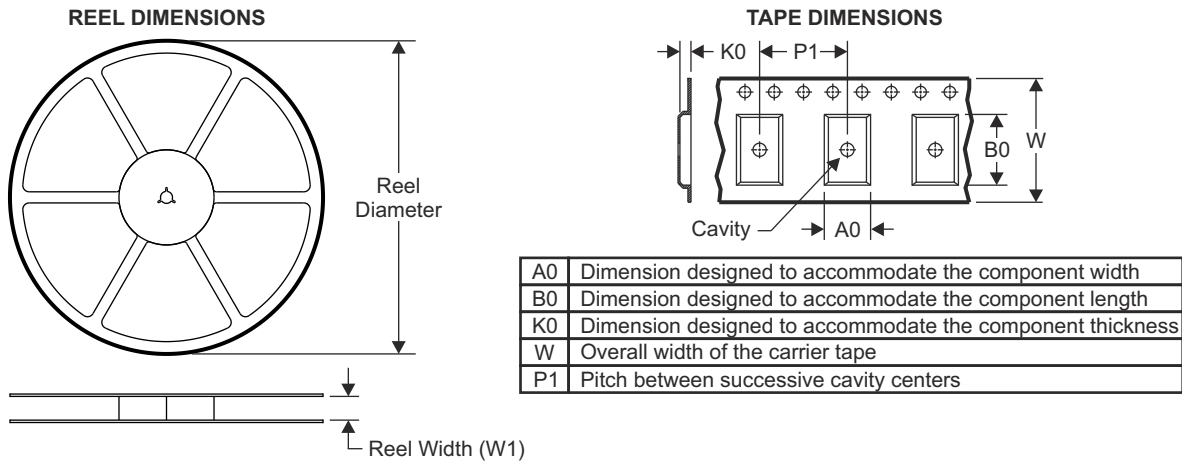
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

12.1 Packaging Information

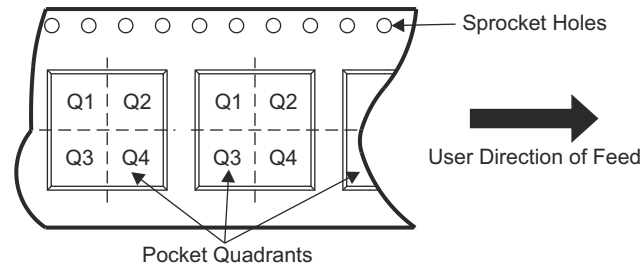
Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish ⁽⁴⁾	MSL Peak Temp ⁽³⁾	Op Temp (°C)	Device Marking ^{(5) (6)}
PTPSI2240QDWQRQ1	PRE_PROD	SOIC	DWQ	11	1000	Green	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	2240QP
PTPSI2240TQDWQRQ1	PRE_PROD	SOIC	DWQ	11	1000	Green	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	2240TQP

- (1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PRE_PROD Unannounced device, not in production, not available for mass market, nor on the web, samples not available.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.
- (2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)
- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device
- (6) Multiple Device markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
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12.2 Tape and Reel Information

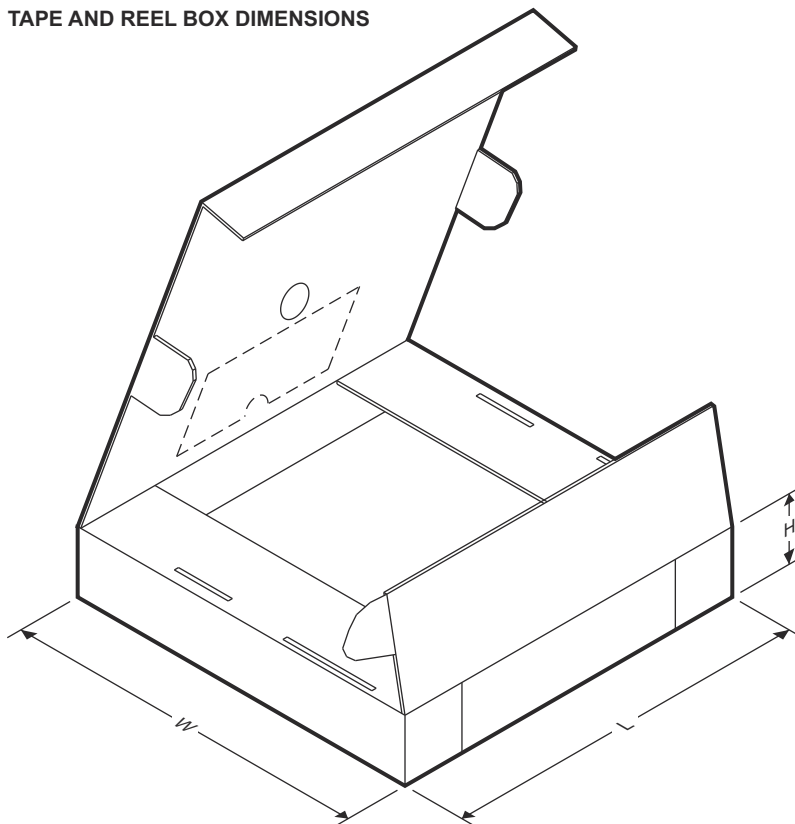


QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
PTPSI2240QDWQRQ1	SOIC	DWQ	11	1000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
PTPSI2240TQDWQRQ1	SOIC	DWQ	11	1000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



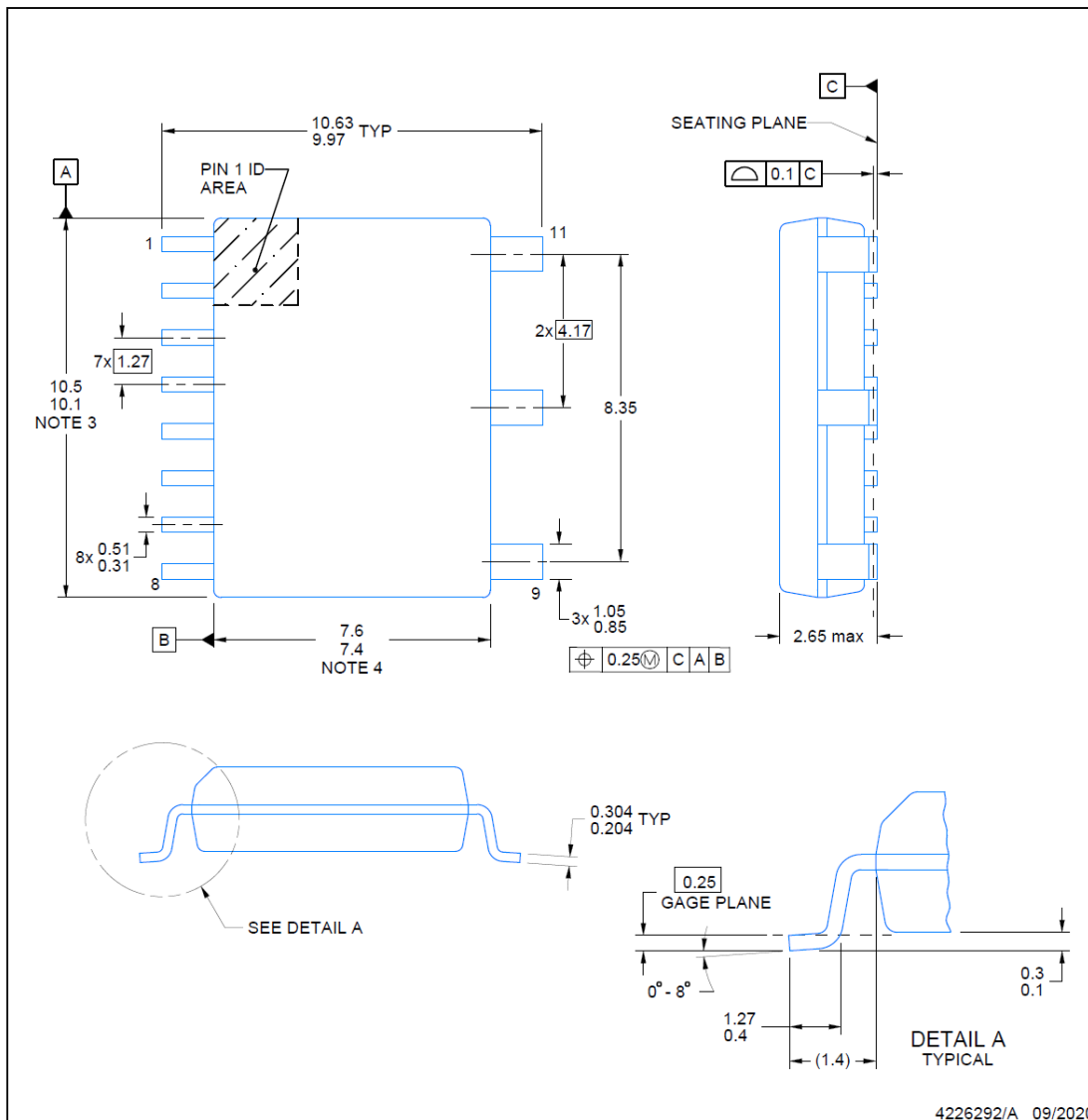
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
PTPSI2240QDWQRQ1	SOIC	DWQ	11	1000	350.0	350.0	43.0
PTPSI2240TQDWQRQ1	SOIC	DWQ	11	1000	350.0	350.0	350.0

PACKAGE OUTLINE

DWQ0011A

SOIC - 2.65 mm max height

SMALL OUTLINE PACKAGE



NOTES:

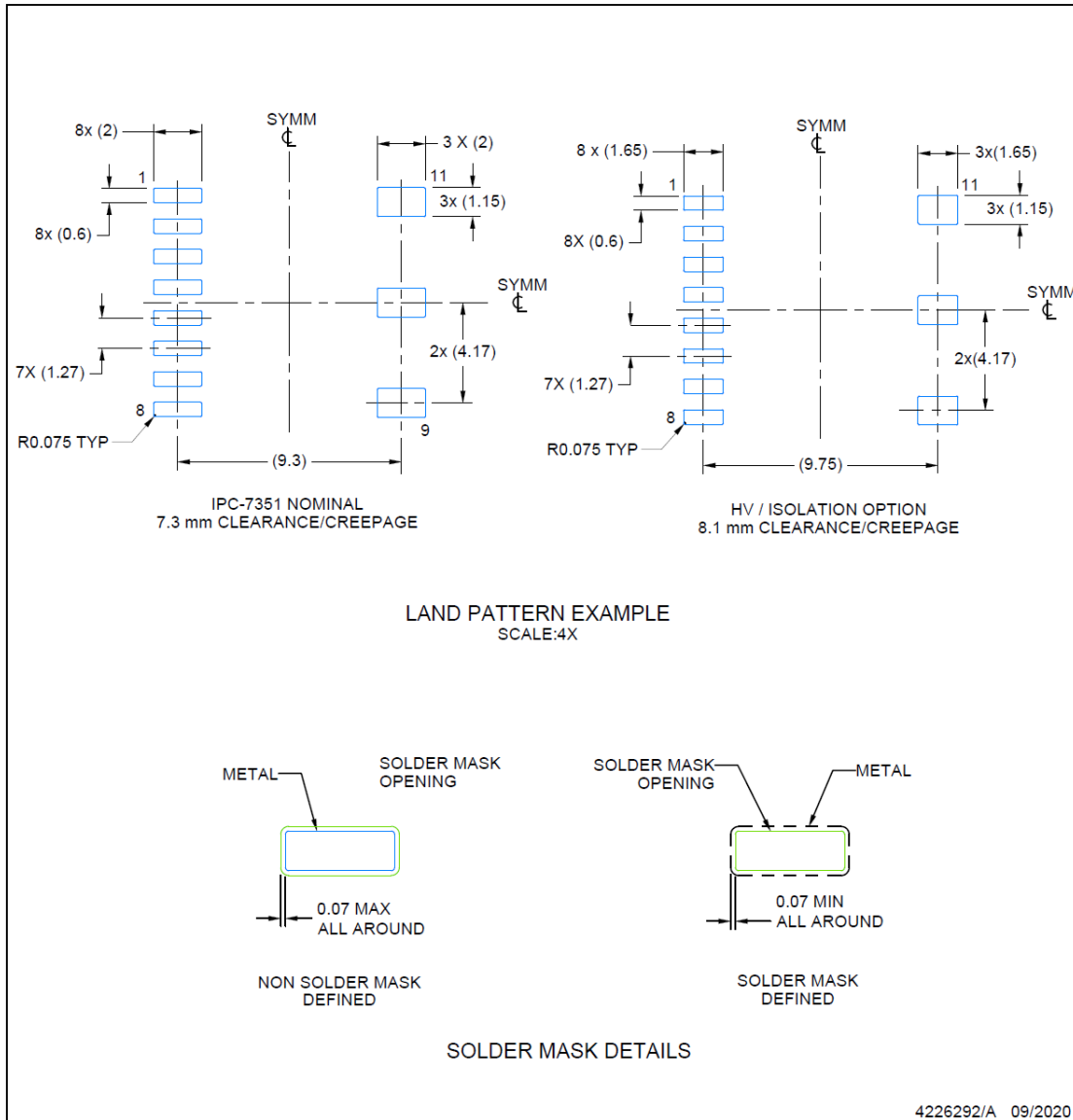
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

DWQ0011A

SOIC - 2.65 mm max height

SOIC



4226292/A 09/2020

NOTES: (continued)

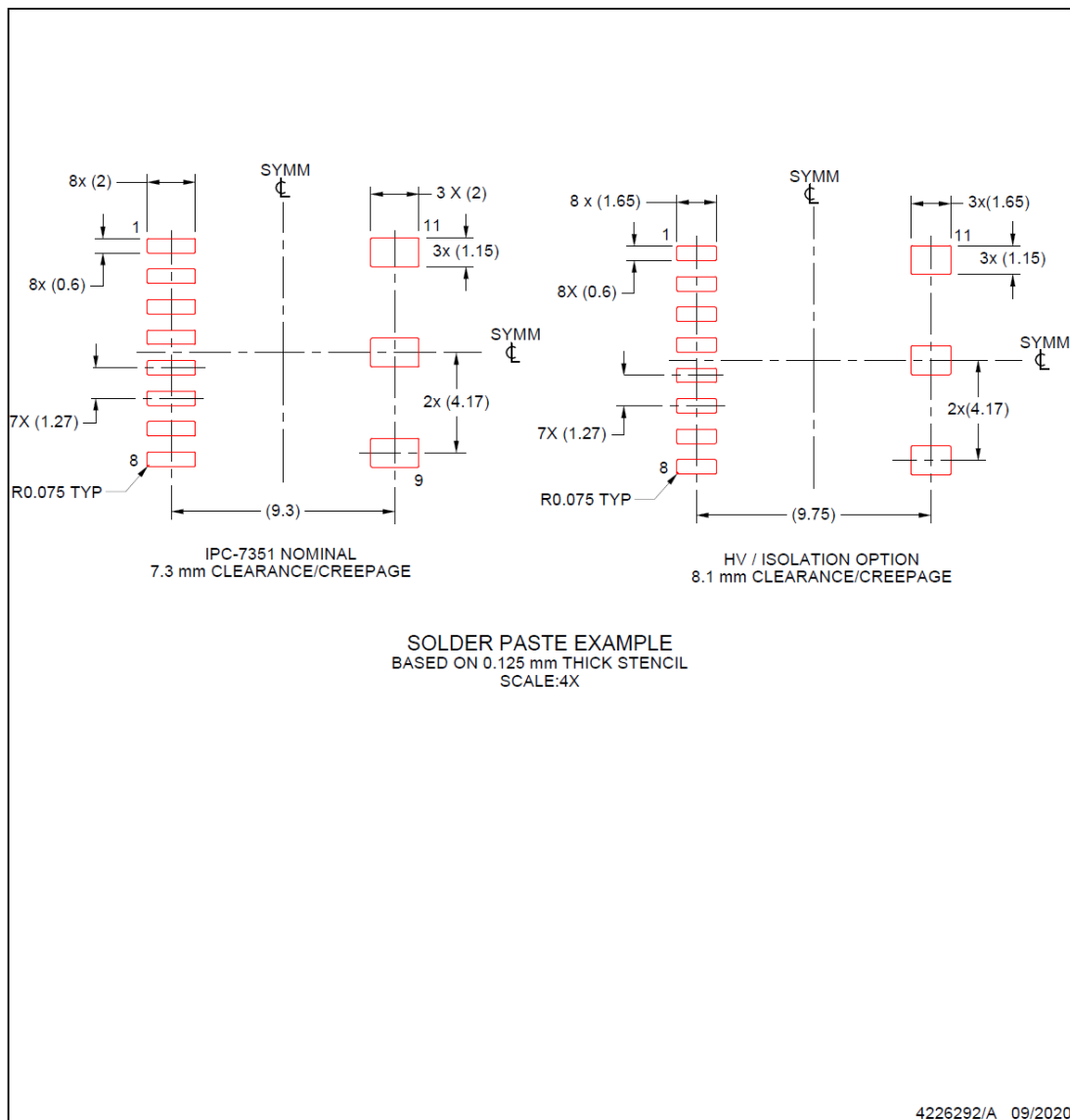
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DWQ0011A

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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